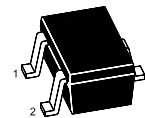
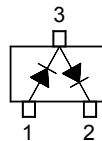


MMBD217SEW

Silicon Epitaxial Planar Switching Diode

Applications

- Ultra high speed switching



SOT-323 Plastic Package

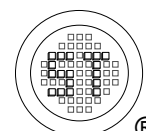
Marking Code: A7

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Repetitive Peak Reverse Voltage	V_{RM}	80	V
Reverse Voltage	V_R	80	V
Average Rectified Forward Current (Single)	$I_{F(AV)}$	100	mA
Maximum (Peak) Forward Current (Single)	I_{FM}	300	mA
Non-repetitive Peak Forward Surge Current ($t = 1 \mu\text{s}$)	I_{FSM}	4	A
Power Dissipation	P_d	200	mW
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 55 to + 150	$^\circ\text{C}$

Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Max.	Unit
Forward Voltage at $I_F = 100 \text{ mA}$	V_F	1.2	V
Reverse Current at $V_R = 70 \text{ V}$	I_R	0.1	μA
Capacitance between Terminals at $V_R = 6 \text{ V}$, $f = 1 \text{ MHz}$	C_T	3.5	pF
Reverse Recovery Time at $I_F = 5 \text{ mA}$, $V_R = 6 \text{ V}$, $R_L = 50 \Omega$	t_{rr}	4	ns



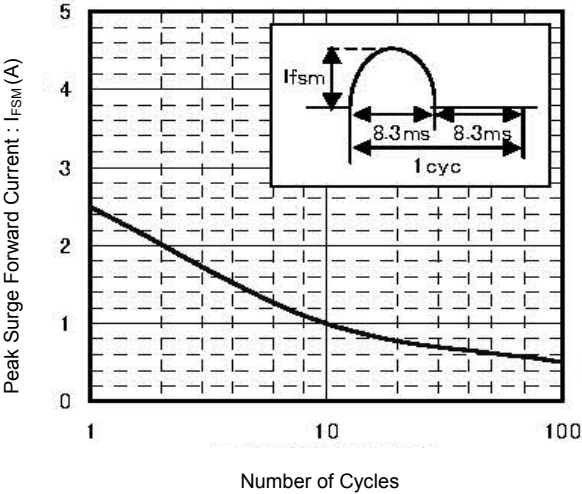


Figure 1. I_{FSM} - Cycle Characteristics

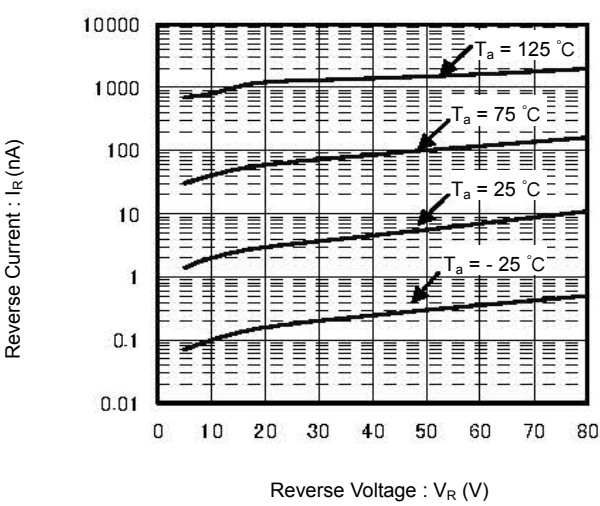


Figure 2. V_R - I_R Characteristics

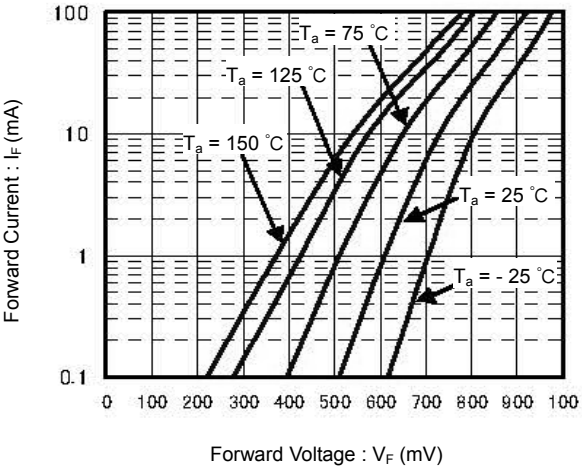


Figure 3. V_F - I_F Characteristics

